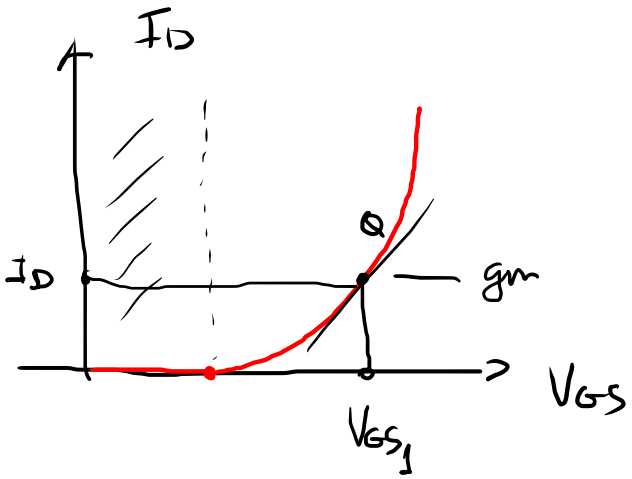
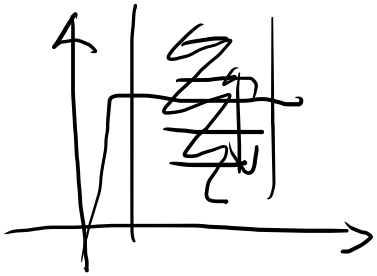
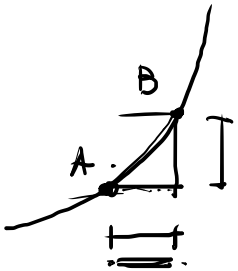
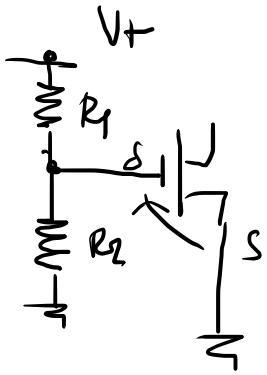
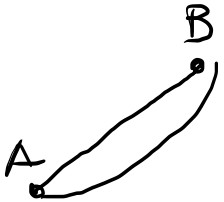








$$g_m = \frac{I_D}{V_{GS}} \sim \frac{\Delta I_D}{\Delta V_{GS}}$$



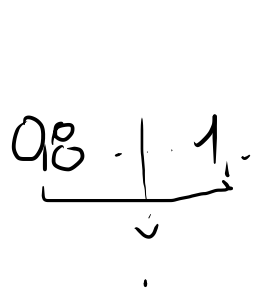
$$g_m = \frac{1}{R_{DS}} \rightsquigarrow \frac{1}{\Omega} \sim \text{Siemens} \quad S \quad \text{o} \quad \Omega^{-1}$$

$$I_{D_B} - I_{D_A} \rightsquigarrow \Delta I_D$$

$$g_m = 2K\left(V_{GS} - V_{GS_{TH}}\right)$$

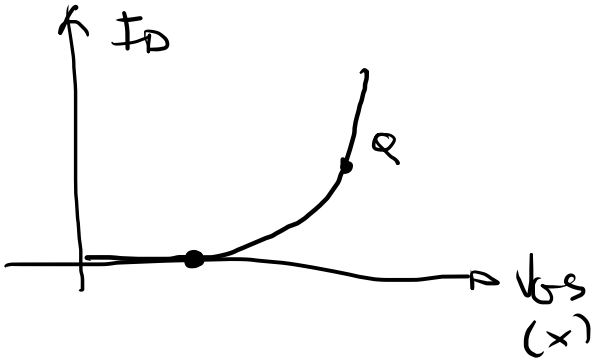
?

$$K = \frac{t}{W \cdot L}$$



$$K = \text{parametro costruttivo MOSfet} = \frac{I_D}{(V_{GS} - V_{TH})^2} = \frac{I_{D\,on}}{(V_{GS\,on} - V_{TH})^2} =$$

$$=$$



$$I_D = K (V_{GS} - V_{TH})^2 \quad \ldots \left(x^2\right)$$

$$(x)$$